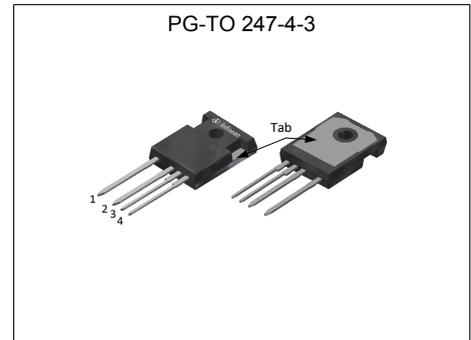


# MOSFET

## 650 V CoolSiC™ M1 SiC Trench Power Device

The 650 V CoolSiC™ is built over the solid silicon carbide technology developed in Infineon in more than 20 years. Leveraging the wide bandgap SiC material characteristics, the 650V CoolSiC™ MOSFET offers a unique combination of performance, reliability and ease of use. Suitable for high temperature and harsh operations, it enables the simplified and cost effective deployment of the highest system efficiency.



### Features

- Optimized switching behavior at higher currents
- Commutation robust fast body diode with low  $Q_{rr}$
- Superior gate oxide reliability
- Best thermal conductivity and behavior
- Lower  $R_{DS(on)}$  and pulse current dependency on temperature
- Increased avalanche capability
- Compatible with standard drivers (recommended driving voltage: 18V)
- Kelvin source provides up to 4 times lower switching losses

### Benefits

- Unique combination of high performance, high reliability and ease of use
- Ease of use and integration
- Suitable for topologies with continuous hard commutation
- Higher robustness and system reliability
- Efficiency improvement
- Reduced system size leading to higher power density

### Potential applications

- SMPS
- UPS (uninterruptable power supplies)
- Solar PV inverters
- EV charging infrastructure
- Energy storage and battery formation
- Class D amplifiers

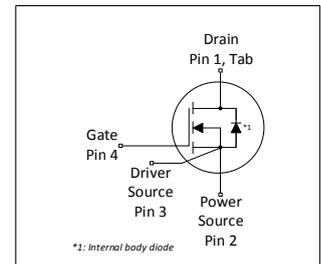
### Product validation

Fully qualified according to JEDEC for Industrial Applications

**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS} @ T_J = 25\text{ °C}$	650	V
$R_{DS(on),typ}$	48	mΩ
$Q_{G,typ}$	33	nC
$I_{D,pulse}$	100	A
$Q_{oss} @ 400\text{ V}$	78	nC
$E_{oss} @ 400\text{ V}$	11.7	μJ

Type / Ordering Code	Package	Marking	Related Links
IMZA65R048M1H	PG-TO 247-4-3	65R048M1	see Appendix A



## Table of Contents

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## 1 Maximum ratings

at  $T_J = 25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	39 24	A	$T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	-	-	100	A	$T_C = 25\text{ °C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	171	mJ	$I_D = 6.4\text{ A}$ , $V_{DD} = 50\text{ V}$ , $L = 8.3\text{ mH}$ ; see table 10
Avalanche energy, repetitive	$E_{AR}$	-	-	0.85	mJ	$I_D = 6.4\text{ A}$ , $V_{DD} = 50\text{ V}$ ; see table 10
Avalanche current, single pulse	$I_{AS}$	-	-	6.4	A	-
MOSFET $dv/dt$ ruggedness	$dv/dt$	-	-	200	V/ns	$V_{DS} = 0...400\text{ V}$
Gate source voltage (recommended driving voltage)	$V_{GS}$	0	-	18	V	AC ( $f > 1\text{ Hz}$ )
Gate source voltage (dynamic)	$V_{GS}$	-5	-	23	V	$t_{pulse,negative} \leq 15\text{ ns}$
Power dissipation	$P_{tot}$	-	-	125	W	$T_C = 25\text{ °C}$
Storage temperature	$T_{stg}$	-55	-	150	°C	-
Operating junction temperature	$T_J$	-55	-	150	°C	-
Mounting torque	-	-	-	60	Ncm	M3 and M3.5 screws
Continuous diode forward current <sup>1)</sup>	$I_S$	-	-	39	A	$T_C = 25\text{ °C}$
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$	-	-	100	A	$T_C = 25\text{ °C}$
Insulation withstand voltage	$V_{ISO}$	-	-	n.a.	V	$V_{rms}$ , $T_C = 25\text{ °C}$ , $t = 1\text{ min}$

<sup>1)</sup> Limited by  $T_{J,max}$

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{J,max}$

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.0	°C/W	-
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62	°C/W	leaded
Thermal resistance, junction - ambient for SMD version	$R_{thJA}$	-	-	-	°C/W	n.a.
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

### 3 Electrical characteristics

at  $T_J = 25\text{ °C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	650	-	-	V	$V_{GS} = 0\text{ V}$ , $I_D = 0.6\text{ mA}$
Gate threshold voltage <sup>1)</sup>	$V_{(GS)th}$	3.5	4.5	5.7	V	$V_{DS} = V_{GS}$ , $I_D = 6\text{ mA}$
Zero gate voltage drain current	$I_{DSS}$	-	1 2	150 -	$\mu\text{A}$	$V_{DS} = 650\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 25\text{ °C}$ $V_{DS} = 650\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 150\text{ °C}$
Gate-source leakage current	$I_{GSS}$	-	-	100	nA	$V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.048 0.063	0.064 -	$\Omega$	$V_{GS} = 18\text{ V}$ , $I_D = 20.1\text{ A}$ , $T_J = 25\text{ °C}$ $V_{GS} = 18\text{ V}$ , $I_D = 20.1\text{ A}$ , $T_J = 150\text{ °C}$
Gate resistance	$R_G$	-	6.0	-	$\Omega$	$f = 1\text{ MHz}$ , open drain

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	1118	-	pF	$V_{GS} = 0\text{ V}$ , $V_{DS} = 400\text{ V}$ , $f = 250\text{ kHz}$
Reverse capacitance	$C_{riss}$	-	13	-	pF	$V_{GS} = 0\text{ V}$ , $V_{DS} = 400\text{ V}$ , $f = 250\text{ kHz}$
Output capacitance <sup>2)</sup>	$C_{oss}$	-	129	168	pF	$V_{GS} = 0\text{ V}$ , $V_{DS} = 400\text{ V}$ , $f = 250\text{ kHz}$
Output charge <sup>2)</sup>	$Q_{oss}$	-	78	101	nC	calculation based on $C_{oss}$
Effective output capacitance, energy related <sup>3)</sup>	$C_{o(er)}$	-	146	-	pF	$V_{GS} = 0\text{ V}$ , $V_{DS} = 0\dots 400\text{ V}$
Effective output capacitance, time related <sup>4)</sup>	$C_{o(tr)}$	-	194	-	pF	$I_D = \text{constant}$ , $V_{GS} = 0\text{ V}$ , $V_{DS} = 0\dots 400\text{ V}$
Turn-on delay time	$t_{d(on)}$	-	14.8	-	ns	$V_{DD} = 400\text{ V}$ , $V_{GS} = 18\text{ V}$ , $I_D = 20.1\text{ A}$ , $R_G = 1.8\text{ }\Omega$ ; see table 9
Rise time	$t_r$	-	12.6	-	ns	$V_{DD} = 400\text{ V}$ , $V_{GS} = 18\text{ V}$ , $I_D = 20.1\text{ A}$ , $R_G = 1.8\text{ }\Omega$ ; see table 9
Turn-off delay time	$t_{d(off)}$	-	17	-	ns	$V_{DD} = 400\text{ V}$ , $V_{GS} = 18\text{ V}$ , $I_D = 20.1\text{ A}$ , $R_G = 1.8\text{ }\Omega$ ; see table 9
Fall time	$t_f$	-	13	-	ns	$V_{DD} = 400\text{ V}$ , $V_{GS} = 18\text{ V}$ , $I_D = 20.1\text{ A}$ , $R_G = 1.8\text{ }\Omega$ ; see table 9

<sup>1)</sup> Tested after 1 ms pulse at  $V_{GS} = +20\text{ V}$

<sup>2)</sup> Maximum specification is defined by calculated six sigma upper confidence bound

<sup>3)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 400 V

<sup>4)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 400 V

**Table 6 Gate charge characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	9	-	nC	$V_{DD} = 400\text{ V}$ , $I_D = 20.1\text{ A}$ , $V_{GS} = 0\text{ to }18\text{ V}$
Gate to drain charge	$Q_{gd}$	-	8	-	nC	$V_{DD} = 400\text{ V}$ , $I_D = 20.1\text{ A}$ , $V_{GS} = 0\text{ to }18\text{ V}$
Gate charge total	$Q_g$	-	33	-	nC	$V_{DD} = 400\text{ V}$ , $I_D = 20.1\text{ A}$ , $V_{GS} = 0\text{ to }18\text{ V}$

**Table 7 Reverse diode characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	$V_{SD}$	-	4.0	-	V	$V_{GS} = 0\text{ V}$ , $I_F = 20.1\text{ A}$ , $T_J = 25\text{ °C}$
Reverse recovery time	$t_{rr}$	-	68	-	ns	$V_R = 400\text{ V}$ , $I_F = 20.1\text{ A}$ , $di_F/dt = 1000\text{ A}/\mu\text{s}$ ; see table 8
Reverse recovery charge	$Q_{rr}$	-	125	-	nC	$V_R = 400\text{ V}$ , $I_F = 20.1\text{ A}$ , $di_F/dt = 1000\text{ A}/\mu\text{s}$ ; see table 8
Peak reverse recovery current	$I_{rrm}$	-	8.4	-	A	$V_R = 400\text{ V}$ , $I_F = 20.1\text{ A}$ , $di_F/dt = 1000\text{ A}/\mu\text{s}$ ; see table 8

### 4 Electrical characteristics diagrams

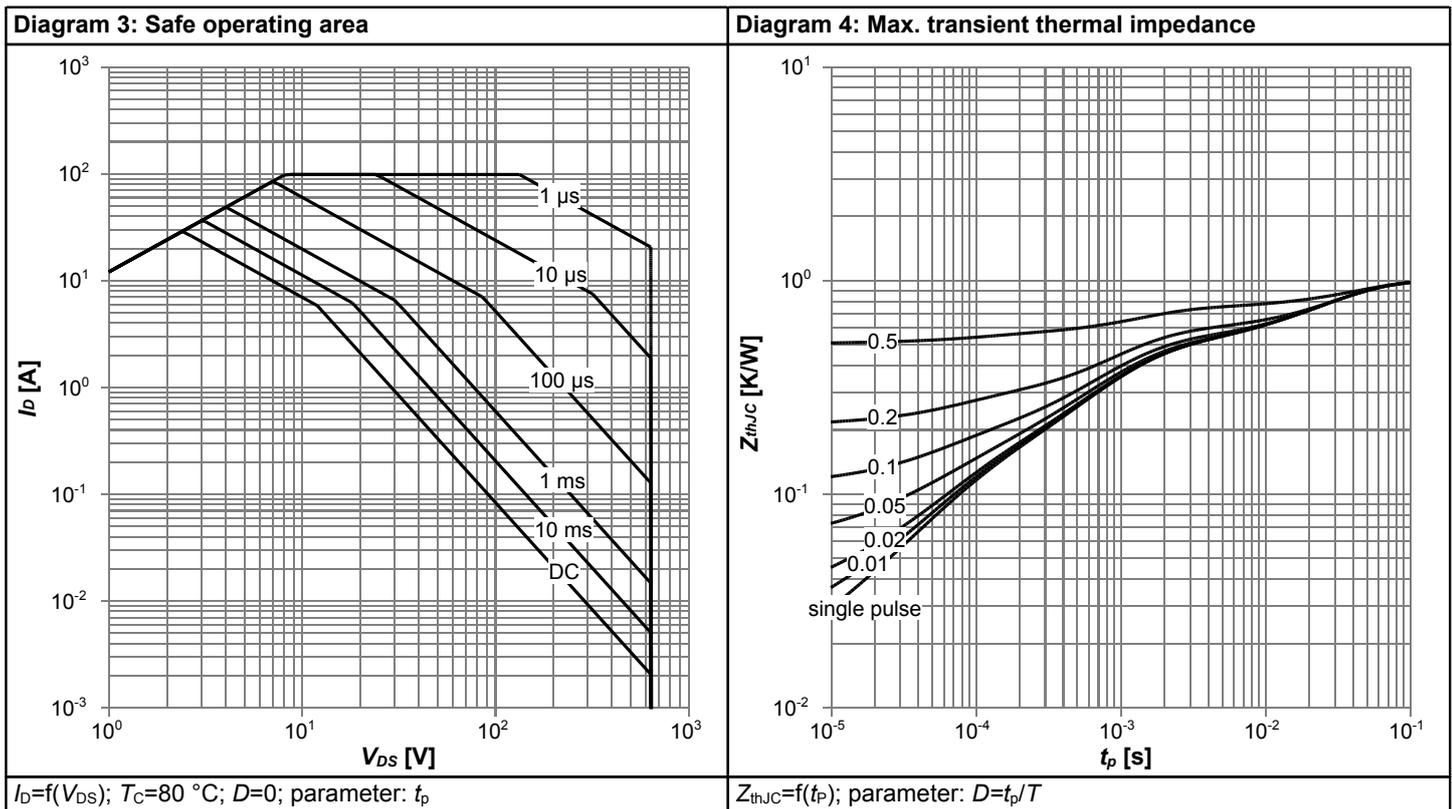
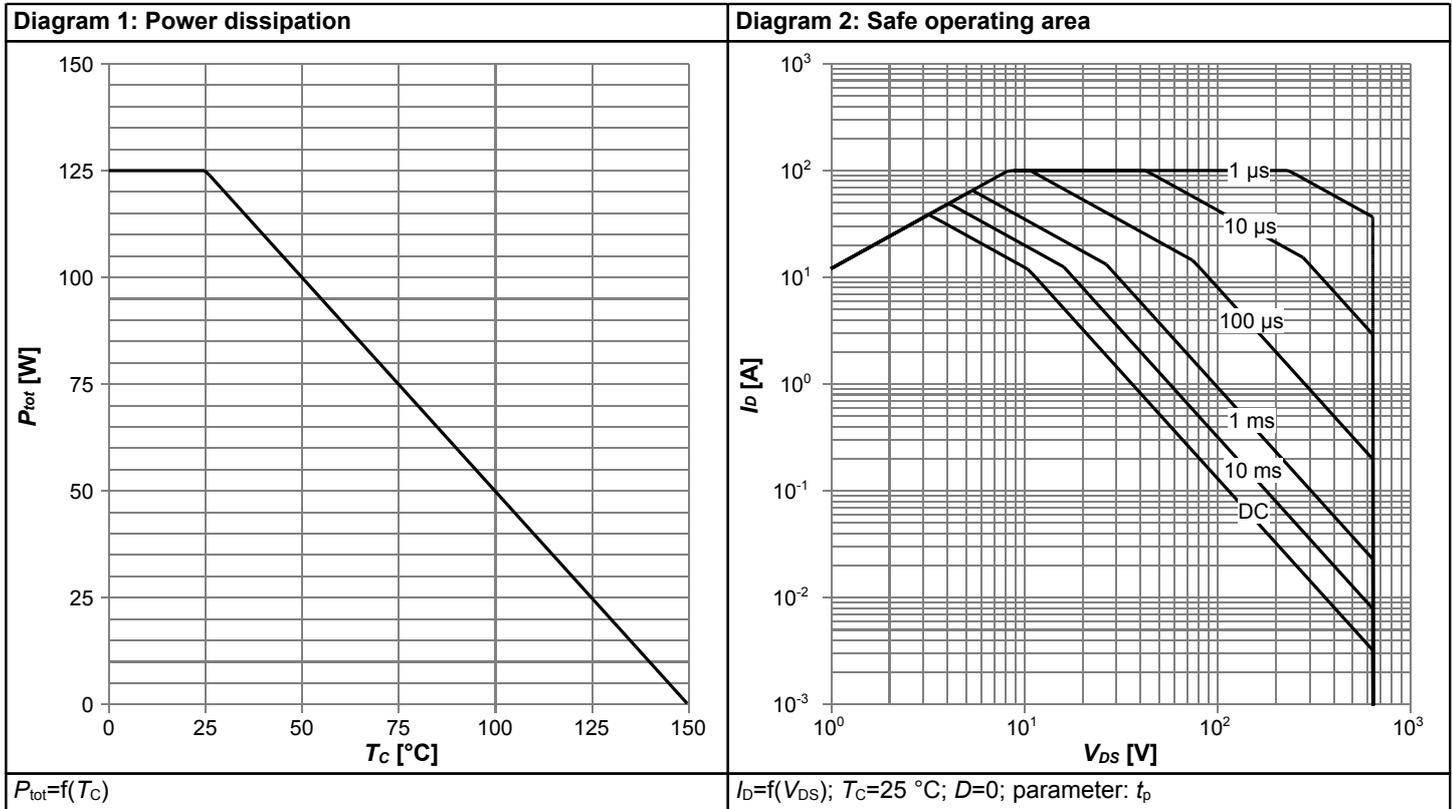
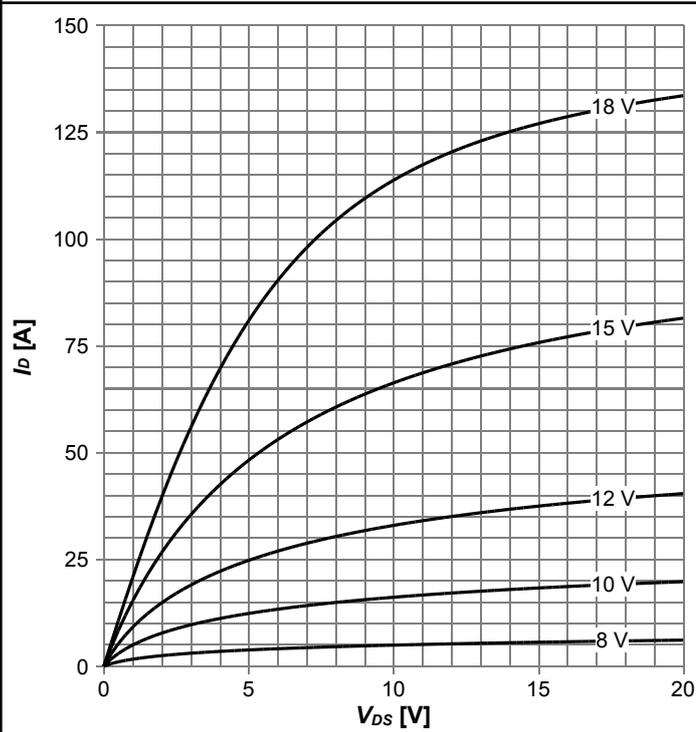
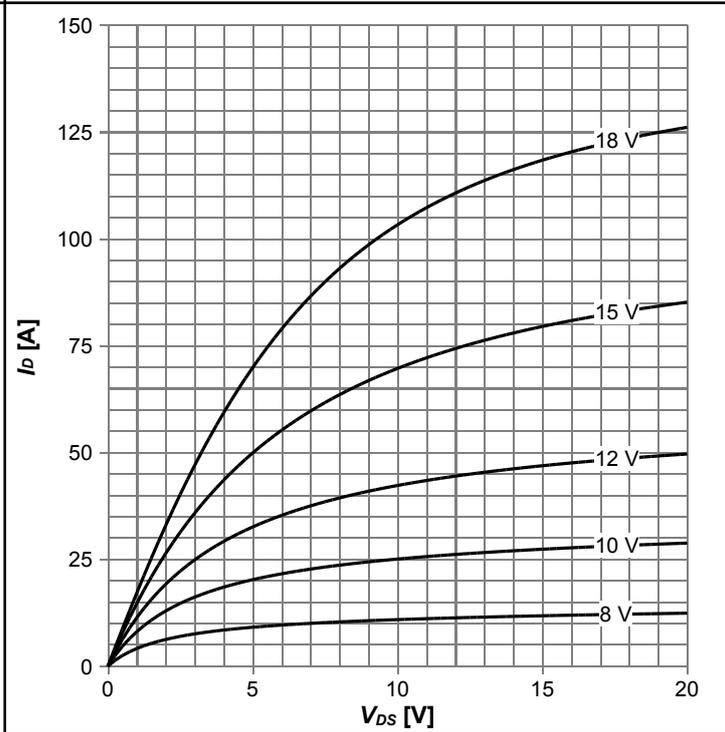


Diagram 5: Typ. output characteristics



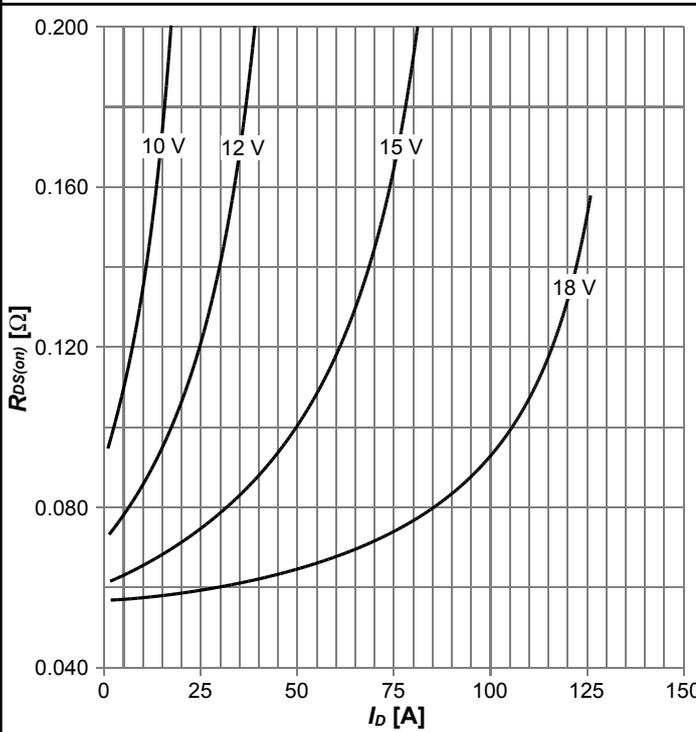
$I_D=f(V_{DS})$ ;  $T_j=25\text{ °C}$ ; parameter:  $V_{GS}$

Diagram 6: Typ. output characteristics



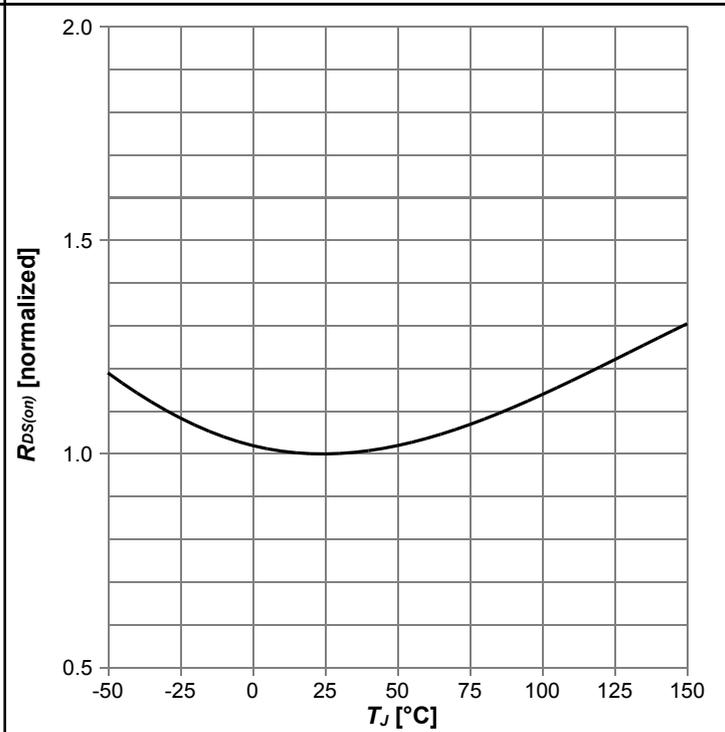
$I_D=f(V_{DS})$ ;  $T_j=125\text{ °C}$ ; parameter:  $V_{GS}$

Diagram 7: Typ. drain-source on-state resistance



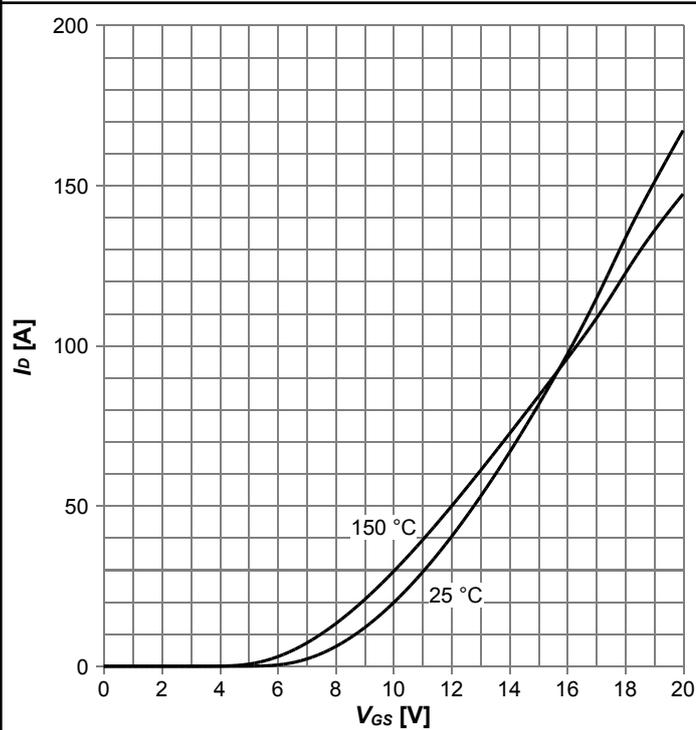
$R_{DS(on)}=f(I_D)$ ;  $T_j=125\text{ °C}$ ; parameter:  $V_{GS}$

Diagram 8: Drain-source on-state resistance



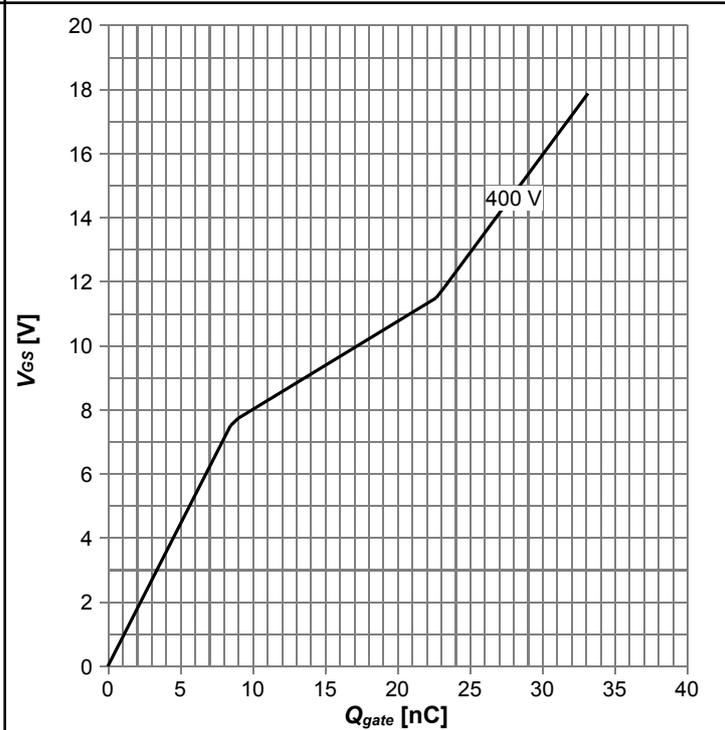
$R_{DS(on)}=f(T_j)$ ;  $I_D=20.1\text{ A}$ ;  $V_{GS}=18\text{ V}$

Diagram 9: Typ. transfer characteristics



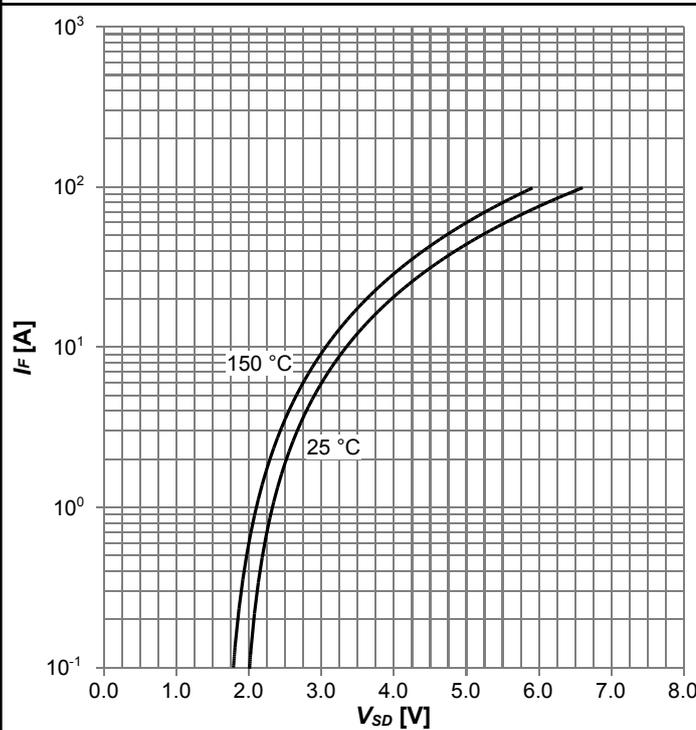
$I_D = f(V_{GS})$ ;  $V_{DS} = 20V$ ; parameter:  $T_j$

Diagram 10: Typ. gate charge



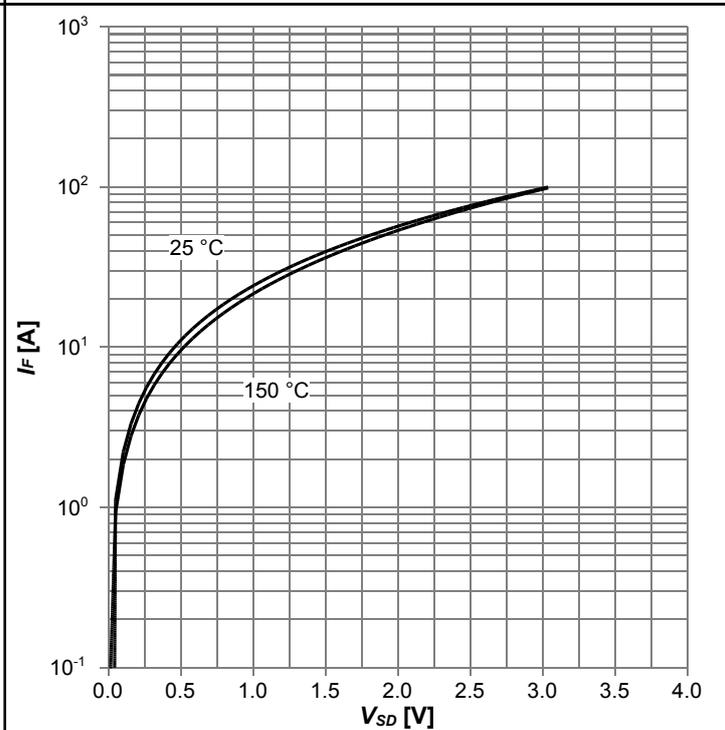
$V_{GS} = f(Q_{gate})$ ;  $I_D = 20.1 A$  pulsed; parameter:  $V_{DD}$

Diagram 11: Forward characteristics of reverse diode



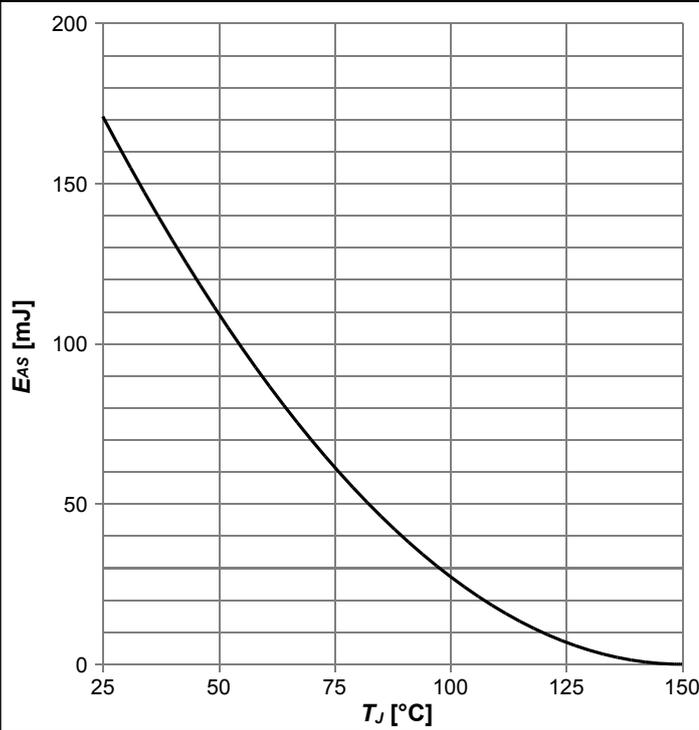
$I_F = f(V_{SD})$ ; parameter:  $T_j$

Diagram 12: Forward characteristics of reverse diode



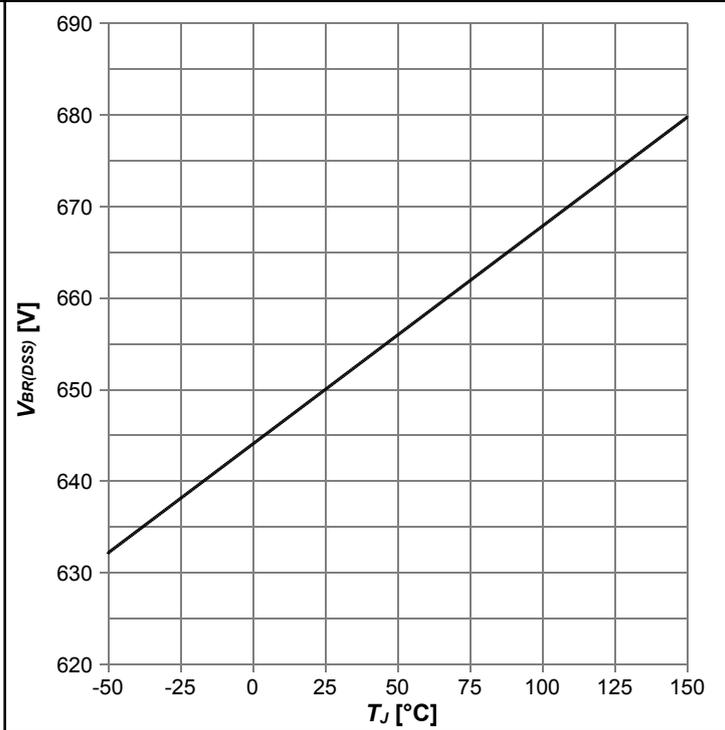
$I_F = f(V_{SD})$ ;  $V_{GS} = 18 V$ ; parameter:  $T_j$

Diagram 13: Avalanche energy



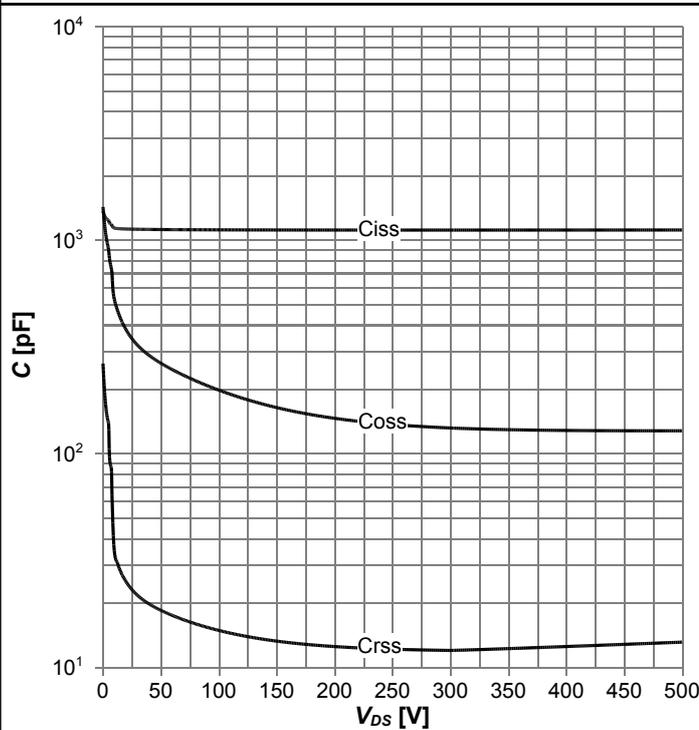
$E_{AS}=f(T_J)$ ;  $I_D=6.4$  A;  $V_{DD}=50$  V

Diagram 14: Drain-source breakdown voltage



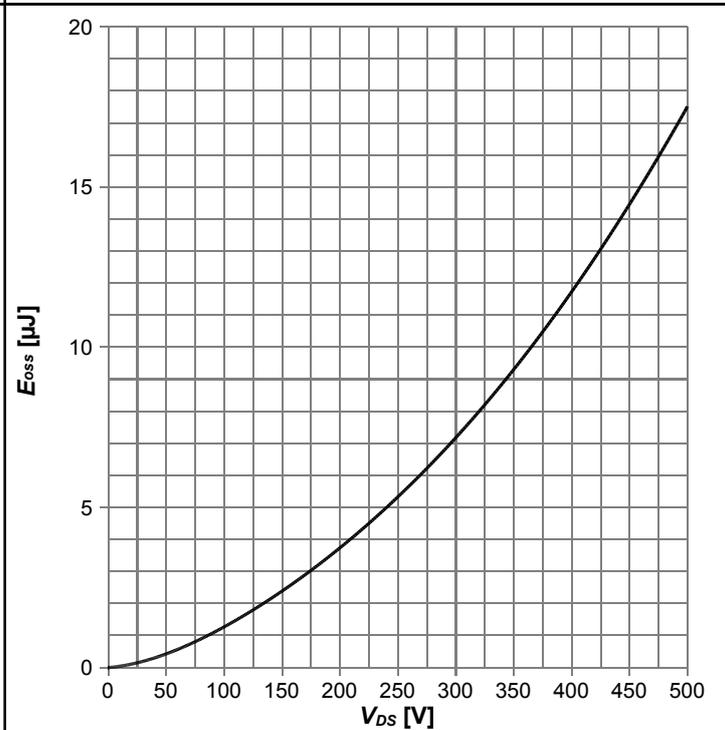
$V_{BR(DSS)}=f(T_J)$ ;  $I_D=0.6$  mA

Diagram 15: Typ. capacitances

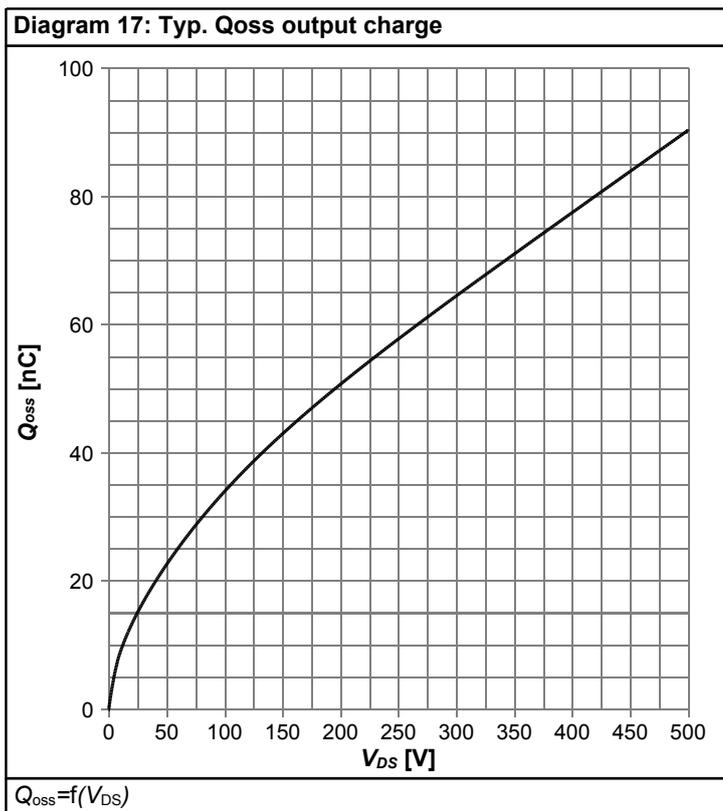


$C=f(V_{DS})$ ;  $V_{GS}=0$  V;  $f=250$  kHz

Diagram 16: Typ. Coss stored energy

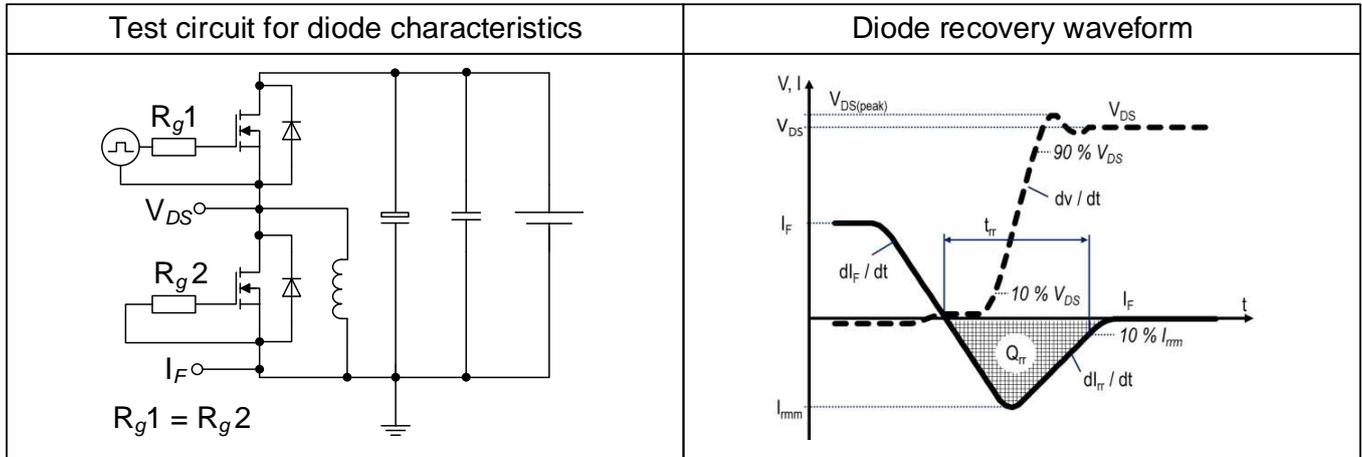


$E_{oss}=f(V_{DS})$

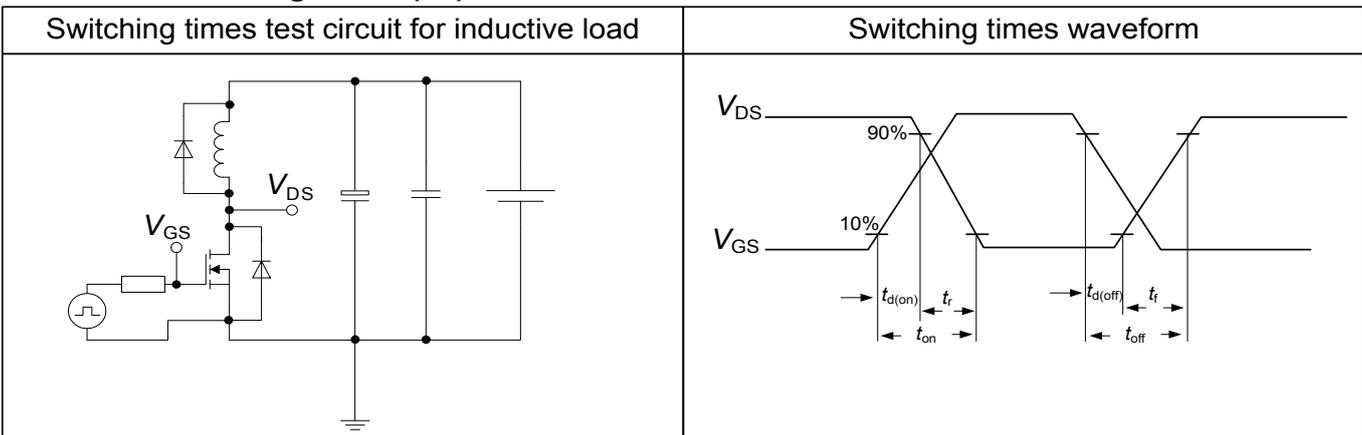


## 5 Test Circuits

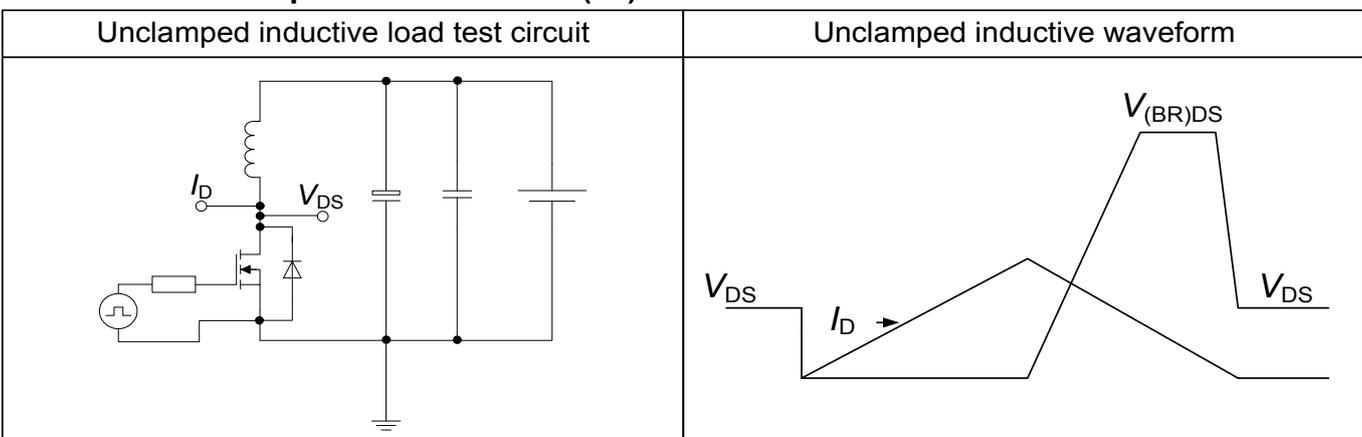
**Table 8 Diode characteristics**



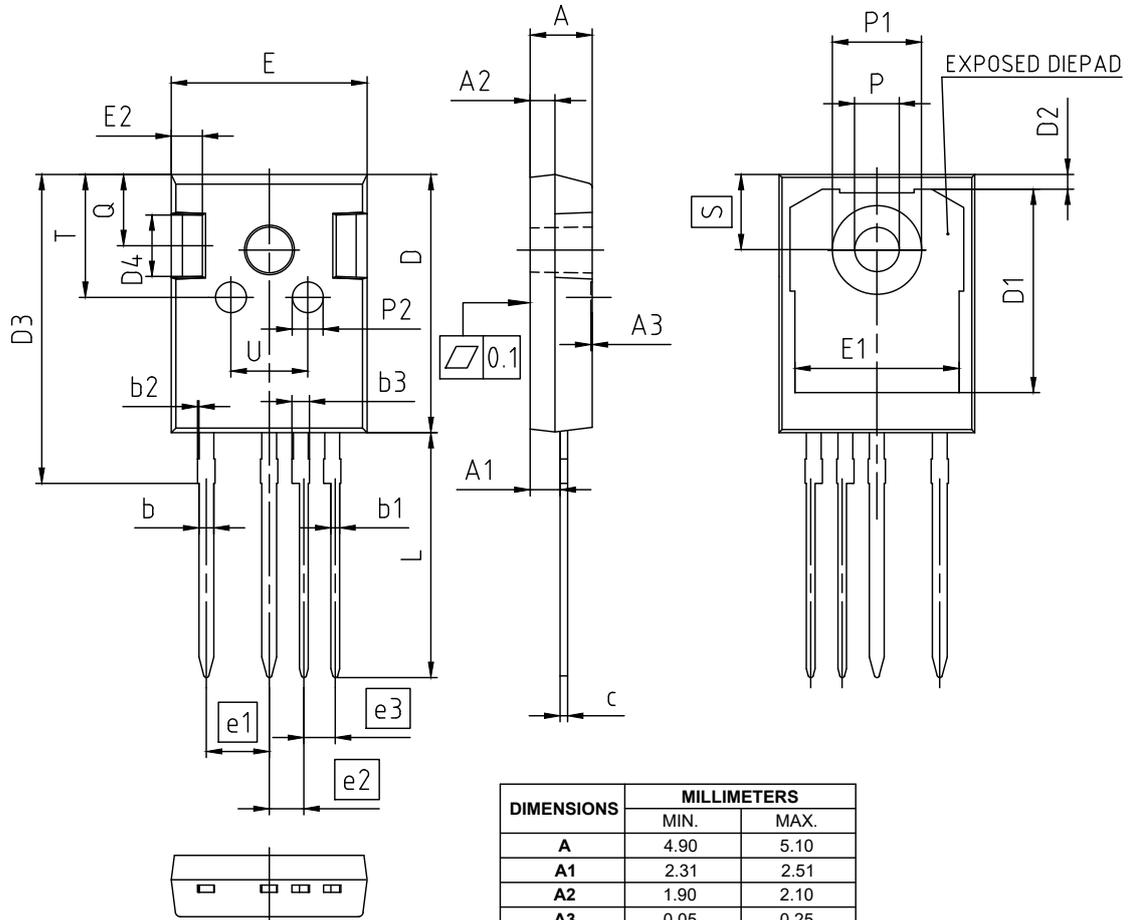
**Table 9 Switching times (ss)**



**Table 10 Unclamped inductive load (ss)**



## 6 Package Outlines



NOTES:  
ALL DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.90	5.10
A1	2.31	2.51
A2	1.90	2.10
A3	0.05	0.25
b	1.10	1.30
b1	0.65	0.79
b2	-	0.20
b3	1.34	1.44
c	0.58	0.66
D	20.90	21.10
D1	16.25	16.85
D2	1.05	1.35
D3	24.97	25.27
D4	4.90	5.10
E	15.70	15.90
E1	13.10	13.50
E2	2.40	2.60
e1	5.08	
e2	2.79	
e3	2.54	
L	19.80	20.10
L1	-	4.30
øP	3.50	3.70
øP1	7.00	7.40
øP2	2.40	2.60
Q	5.60	6.00
S	6.15	
T	9.80	10.20
U	6.00	6.40

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Figure 1 Outline PG-TO 247-4-3, dimensions in mm

## **7 Appendix A**

### **Table 11 Related Links**

- **IFX CoolSiC M1 Webpage:** [www.infineon.com](http://www.infineon.com)
- **IFX CoolSiC M1 application note:** [www.infineon.com](http://www.infineon.com)
- **IFX CoolSiC M1 simulation model:** [www.infineon.com](http://www.infineon.com)
- **IFX Design tools:** [www.infineon.com](http://www.infineon.com)

## Revision History

IMZA65R048M1H

**Revision: 2019-12-16, Rev. 2.0**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2019-12-16	Release of final version

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